

100V N-Channel Power MOSFET

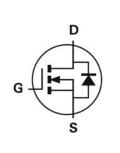
V<sub>DSS</sub>, 100V

 $R_{DS(ON)}$  ,  $80m\Omega$  (max.) @ VGS=10V  $R_{DS(ON)}$  ,  $94m\Omega$  (max.) @ VGS=4.5V

I<sub>D</sub>, 3.4A







Description	Features
The SG100N13S uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Lithium-Ion Secondary Batteries</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

**Ordering Information** 

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG100N13S	Halogen-Free	SOP-8	S	Tape & Reel	3,000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Param	eter	Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Drain Current-Continuous	T <sub>A</sub> =25°C	I-	3.4	Α
Drain Current-Continuous	T <sub>A</sub> =70°C	ID I	2.7	Α
Drain Current-Pulsed Note 1	<u>.</u>	I <sub>DM</sub>	10	Α
Avalanche Current		las	12	Α
Avalanche Energy, L=0.1mH		E <sub>AS</sub>	7.2	mJ
Maximum Dawar Dissination	T <sub>A</sub> =25°C	D	1.5	W
Maximum Power Dissipation	T <sub>A</sub> =70°C	P <sub>D</sub>	0.9	W
Storage Temperature Range	·	T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

**Thermal Resistance Ratings** 

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	RθJA	Steady State	-	-	85	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	25	°C/W

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#### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage	I <sub>GSS</sub>	$V_{GS}=\pm20V$ , $V_{DS}=0V$	ı	ı	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250μA	1.0	-	2.5	V
Drain-Source On-State Resistance	Б	V <sub>GS</sub> =10V, I <sub>DS</sub> =5A	-	-	80	mΩ
	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>DS</sub> =3A	-	-	94	mΩ
Forward Transconductance	gfs	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	-	20	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	1488	-	
Output Capacitance	Coss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	-	58	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	35	-	1
Gate Resistance	Rg	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz	-	2	-	Ω

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	4	-	
Rise Time	tr	V <sub>DS</sub> =50V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V,	-	7.4	-	200
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>GEN</sub> =3.3Ω	-	40	-	ns
Fall Time	t <sub>f</sub>		-	13	-	
Total Gate Charge at 10V	Qg		-	25.4	-	
Gate to Source Gate Charge	Q <sub>gs</sub>	V <sub>DS</sub> =80V, I <sub>DS</sub> =2A, V <sub>GS</sub> =10V	-	3.6	-	nC
Gate to Drain "Miller" Charge	Q <sub>gd</sub>		-	4.6	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =1A	-	-	1.2	V
Continuous Source Current	Is	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	-	-	1.6	Α
Pulsed Source Current	Ism	VG-VD-UV, FOICE CUITEIIL	-	-	5	Α
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I⊧=1A, dl/dt=100A/µs	-	15	-	ns
Body Diode Reverse Recovery Charge	Qrr	1F-1A, αΙ/αι-100A/μS	-	9.5	-	nC

#### Notes:

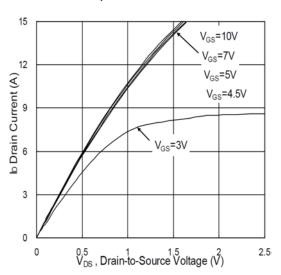
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>θJC</sub> is guaranteed by design while R<sub>θJA</sub> is determined by the user's board design. R<sub>θJA</sub> shown below for single device operation on FR-4 in still air.



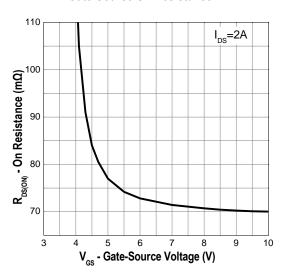
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#### **Typical Operating Characteristics**

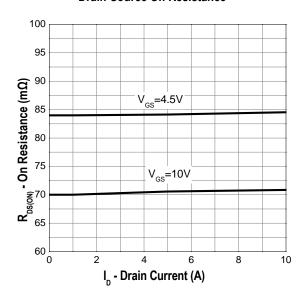
#### **Output Characteristics**



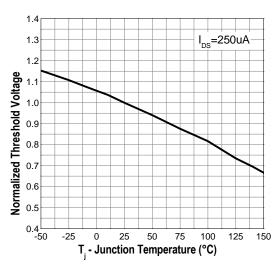
#### **Gate-Source On Resistance**



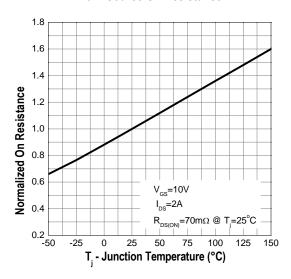
#### **Drain-Source On Resistance**



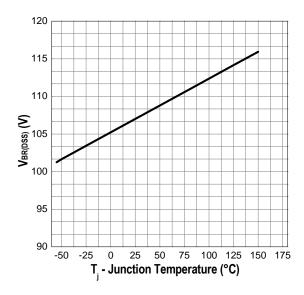
#### **Gate Threshold Voltage**



#### **Drain-Source On Resistance**



#### **Source-Drain Diode Forward**

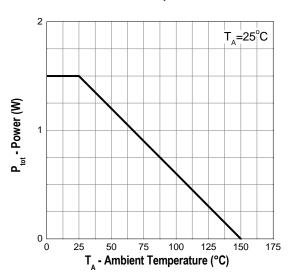




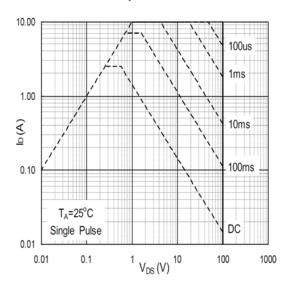
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#### **Typical Operating Characteristics (Cont.)**

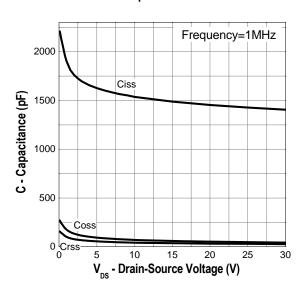
#### **Power Dissipation**



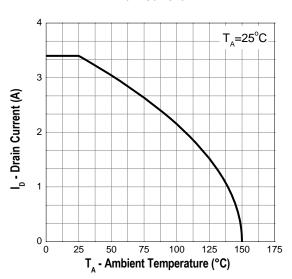
#### **Safe Operation Area**



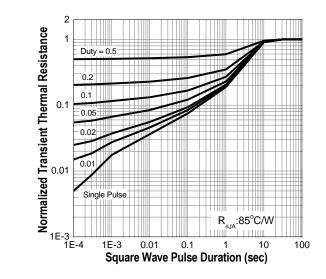
Capacitance



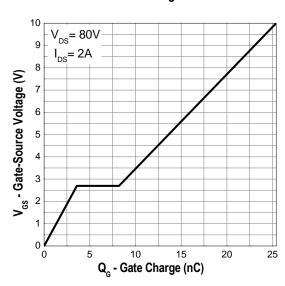
#### **Drain Current**



#### **Transient Thermal Impedance**



**Gate Charge** 





# SG100N13S 100V N-Channel Power MOSFET

#### **Marking Information**

SOP-8 (S)	Marking Rule
Laser Marking	Line 1 : Device Name
	SG100N13S
	Line 2 : Date Code
SG100N13S	YYMMXXX
YYMMXXX	YY: Year Code
	MM: Month Code
	XXX : Serial Number



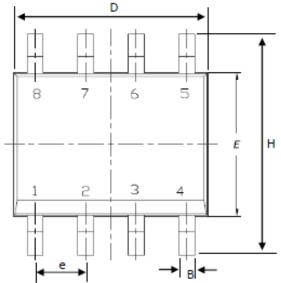


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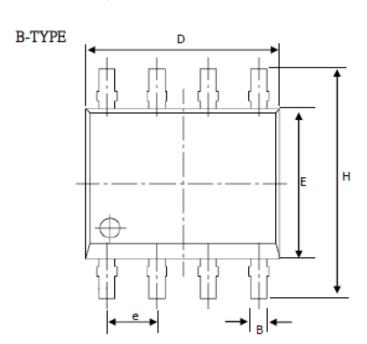
#### **Package of Dimension**

G-TYPE





Symbol	Min	Nor	Max
Α	1.35	1.55	1.75
A1	0.10	0.18	0.25
В	0.31	0.41	0.51
С	0.17	0.21	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27	1.27	1.27
Н	5.80	6.00	6.20
Ĺ	0.40	0.84	1.27
α	0.00	4.00	8.00



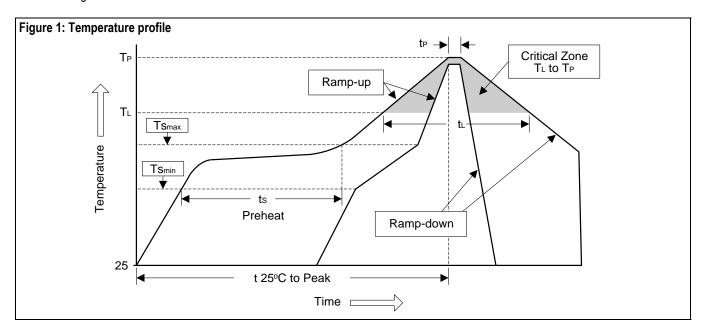


- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



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- **Soldering Methods for Silicongear's Products**1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T <sub>L</sub> to T <sub>P</sub> )	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 ooo	20 to 40 cos
Temperature (t <sub>P</sub> )	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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